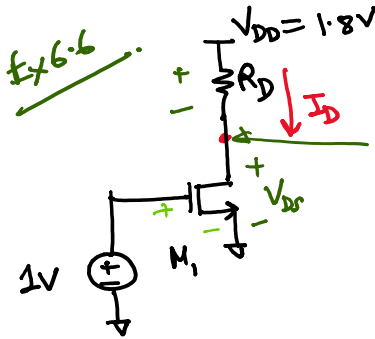


# ECF 310. Lecture 20

Friday, March 2, 2018 10:31 AM



$$R_D = 5k\Omega$$

$$k_{Pn} = \mu_n C_{ox} = \frac{100 \mu A}{V^2}$$

$$\frac{W}{L} = \frac{2 \mu m}{0.18 \mu m}$$

$$V_{THN} = 0.4V$$

Assume  $M_1$  is in SAT

$$\lambda = 0$$

$$I_D = \frac{1}{2} k_{Pn} \left( \frac{W}{L} \right) (V_{GS} - V_{THN})^2$$

$$= 20 \mu A$$

$$V_{DS} = V_{DD} - I_D \cdot R_D = 0.8V$$

$$V_{DS,sat} = V_{GS} - V_{THN} = 1 - 0.4 = 0.6V$$

$$\left. \begin{array}{l} \text{Yes } M_1 \text{ is in SAT, } I_D = 20 \mu A \\ V_{DS} = 0.8V \end{array} \right\} \text{Ans.}$$

$$R_D = 8k\Omega$$

$$V_{DS} = V_{DD} - I_D \times 8k\Omega = 1.8 - \frac{20 \mu A \times 8k}{1.6} = 0.2V$$

$$0.2 < 0.6V$$

$$V_{DS} \quad V_{DS,sat}$$

$M_1$  is now in TRIODE.

$$\frac{V_{DD} - V_{DS}}{R_D} = I_D = k_{Pn} \left( \frac{W}{L} \right) \left[ (V_{GS} - V_{THN}) V_{DS} - \frac{V_{DS}^2}{2} \right]$$

$$\text{Let } x \equiv V_{DS}$$

$$1.8 - x = 100 \mu A \times 8k \times \left( \frac{2}{0.18} \right) \left[ 0.6x - \frac{x^2}{2} \right]$$

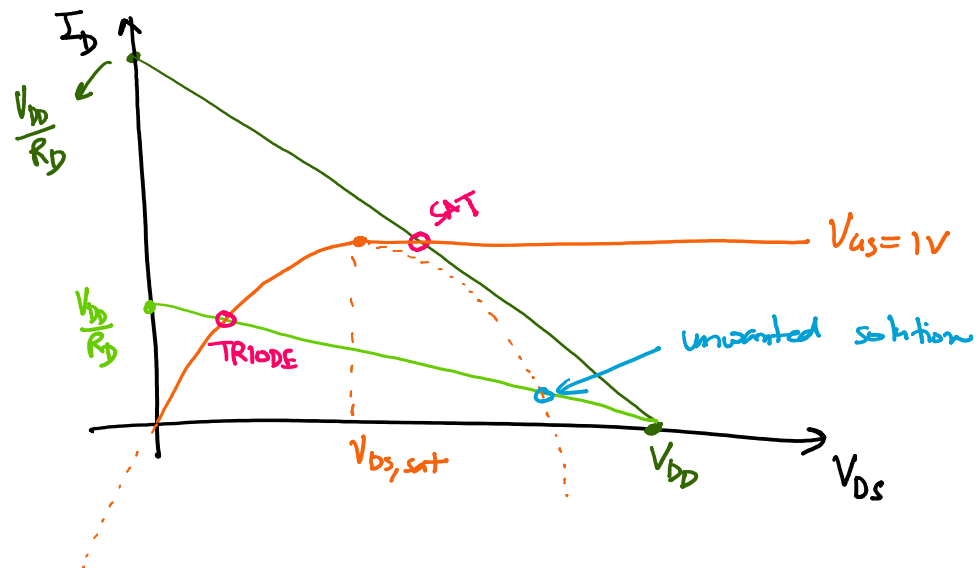
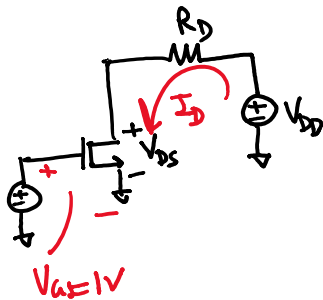
$$\Rightarrow 1.8 - x = 5.333x - 4.444x^2$$

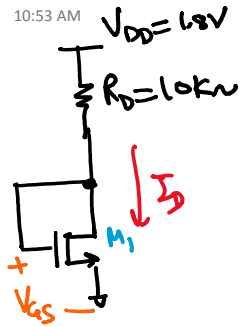
$$\Rightarrow 4.444x^2 - 6.333x + 1.8 = 0$$

Solve for  $x = \underline{0.392V}$ ,  ~~$1.033V$~~   $\rightarrow$  This would mean we are in SAT

$$V_{DS} = 0.392V$$

$$I_D = \frac{V_{DD} - V_{DS}}{R_D} = \frac{1.8 - 0.392}{8k} = \boxed{176\mu A}$$





Diode-connected MOSFET → can never be in Triode

$$V_{DS} = V_{GS}$$

for  $M_1$  to be ON  $\Rightarrow V_{GS} > V_{THN}$

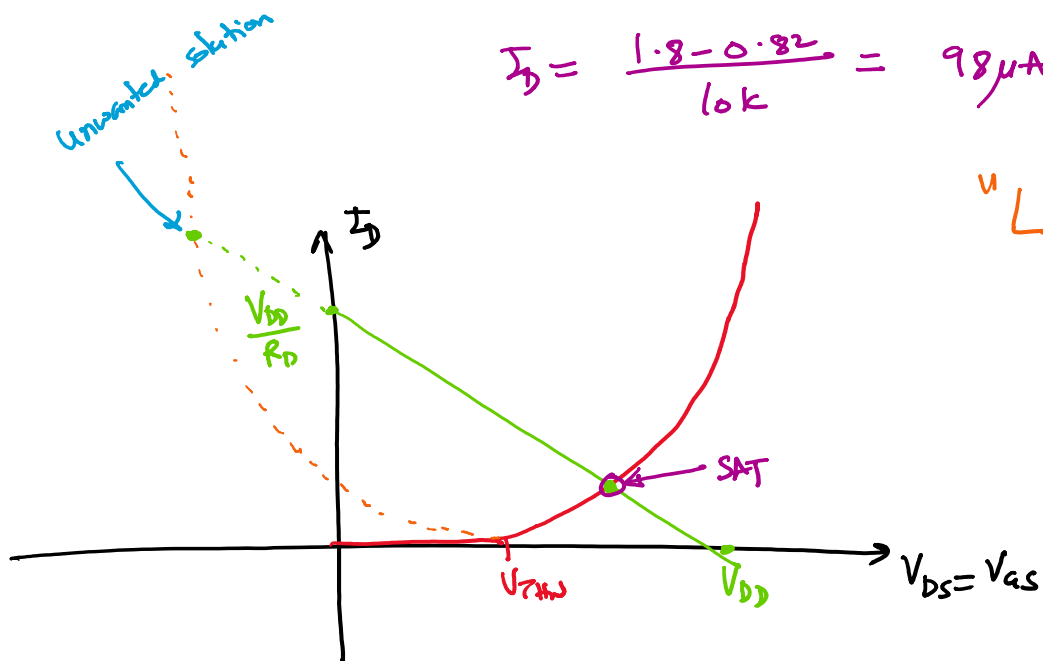
$$\boxed{\lambda = 0}$$

$$\frac{V_{DD} - V_{GS}}{R_D} = I_D = \frac{1}{2} k_{Pn} [V_{GS} - V_{THN}]^2$$

$$x = V_{GS} = 0.82, -0.2$$

$$V_{GS} = V_{DS} = 0.82 \text{ V}$$

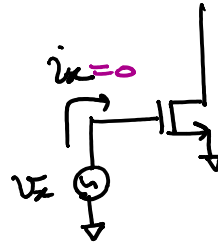
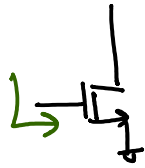
$$I_D = \frac{1.8 - 0.82}{10k} = 98 \mu\text{A}$$



"Loihi chip  
from Intel"

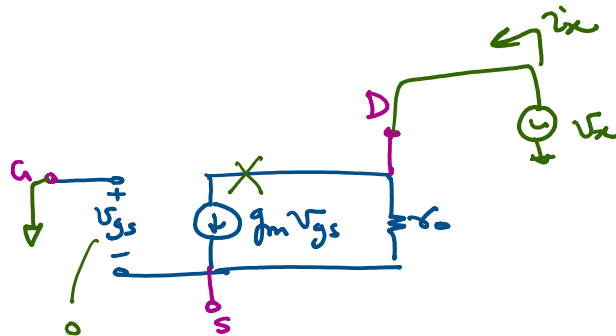
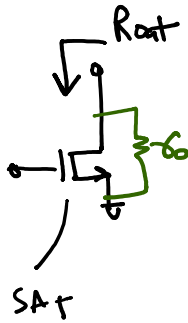
low-frequency

AC analysis ← small signal MOSFET model



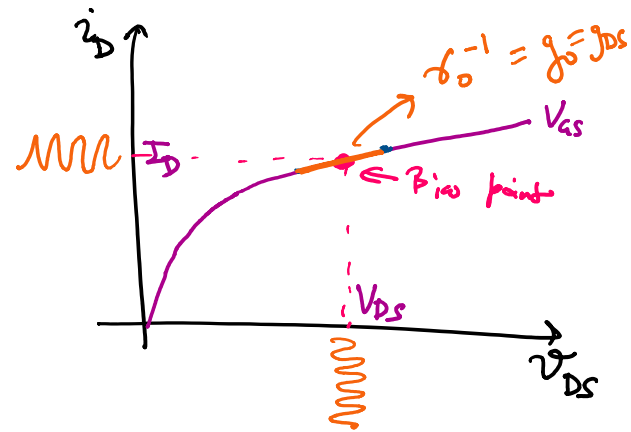
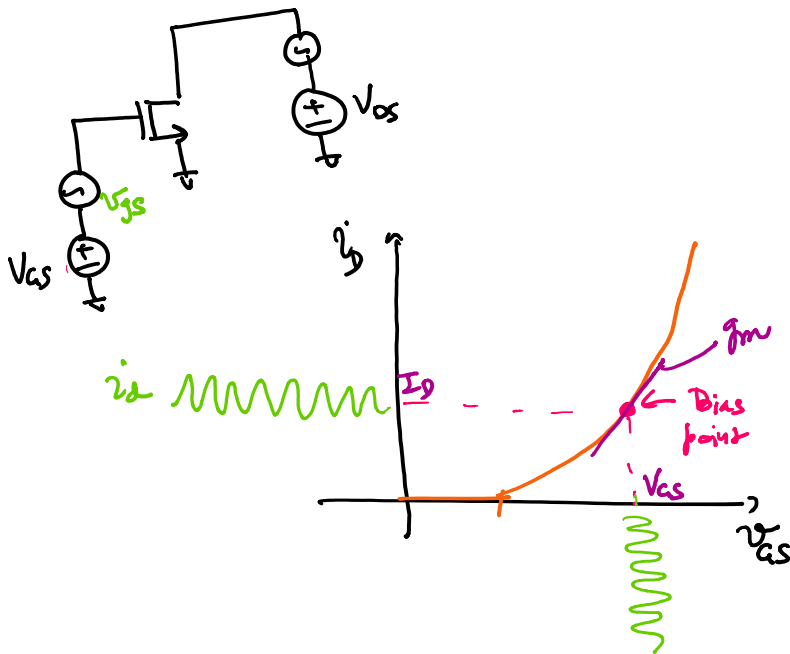
$R_{in} \rightarrow \infty$

$$Z_{in} = R_{in} = \frac{v_x}{i_x}$$



$$R_{out} = \frac{v_x}{i_x} = r_o$$

Biasing → All DC voltages & currents in the circuit are defined



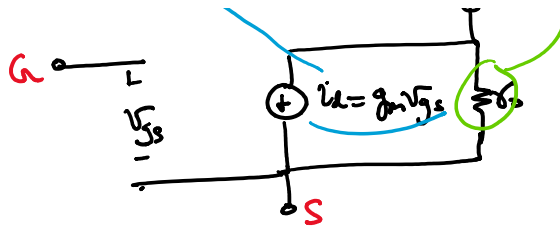
$$g_m \equiv \text{Transconductance} = \left. \frac{\partial I_D}{\partial v_{GS}} \right|_{v_{GS} = V_{GS}}$$

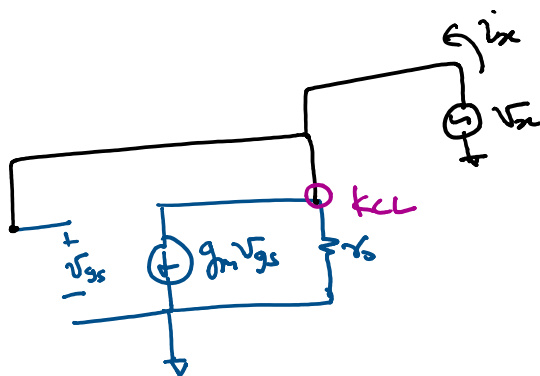
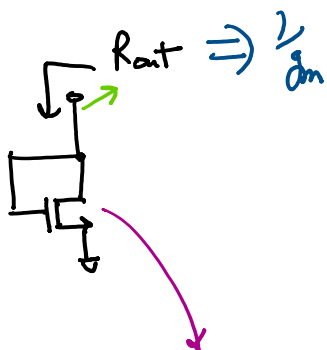
$$\begin{aligned} \text{total } v_{GS} &= V_{GS} + v_{gs} \\ v_{DS} &= V_{DS} + v_{ds} \\ i_D &= I_D + i_d \end{aligned}$$

$$r_o = \left. \left( \frac{\partial I_D}{\partial v_{DS}} \right)^{-1} \right|_{v_{DS} = V_{DS}}$$

$$\begin{aligned} i_d &= g_m v_{gs} \\ i_d &= \frac{v_{ds}}{r_o} \end{aligned} \quad \left. \begin{array}{l} \text{Small-signal equation} \\ \hookrightarrow \text{linear} \end{array} \right\}$$

The figure shows a small-signal equivalent circuit diagram. It consists of a dependent current source  $i_d = g_m v_{gs}$  in parallel with an output resistance  $r_o$ . The input voltage  $v_{gs}$  is applied across the current source, and the output voltage  $v_{ds}$  is applied across the output resistance.





$$v_{gs} = v_x$$

$$i_x - \frac{v_x}{r_o} - g_m v_x = 0$$

$$i_x = v_x \left( g_m + \frac{1}{r_o} \right)$$

$$R_{out} = \frac{v_x}{i_x} = \frac{1}{g_m + 1/r_o} = \frac{1}{g_m} \parallel r_o \approx \frac{1}{g_m}$$

$$r_o \Rightarrow \frac{1}{g_m}$$